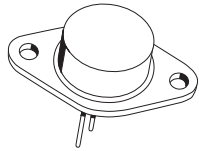


2N6383
2N6384
2N6385

**NPN SILICON POWER
DARLINGTON TRANSISTOR**



TO-3 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3683 SERIES types are NPN Silicon Power Darlington Transistors designed for power amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

Collector-Base Voltage	V_{CBO}	40	60	80	V
Collector-Emitter Voltage	V_{CEX}	40	60	80	V
Collector-Emitter Voltage	V_{CEO}	40	60	80	V
Emitter-Base Voltage	V_{EBO}		5.0		V
Collector Current	I_C		10		A
Peak Collector Current	I_{CM}		15		A
Base Current	I_B		250		mA
Power Dissipation	P_D		100		W
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 to +200		$^\circ\text{C}$
Thermal Resistance	θ_{JC}		1.75		$^\circ\text{C/W}$

SYMBOL	2N6383	2N6384	2N6385	UNITS
V_{CBO}	40	60	80	V
V_{CEX}	40	60	80	V
V_{CEO}	40	60	80	V
V_{EBO}		5.0		V
I_C		10		A
I_{CM}		15		A
I_B		250		mA
P_D		100		W
T_J, T_{stg}		-65 to +200		$^\circ\text{C}$
θ_{JC}		1.75		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEV}	$V_{CEV}=\text{Rated } V_{CEO}, V_{BE(\text{off})}=1.5\text{V}$		300	μA
I_{CEV}	$V_{CEV}=\text{Rated } V_{CEO}, V_{BE(\text{off})}=1.5\text{V}, T_C=150^\circ\text{C}$		3.0	mA
I_{CEO}	$V_{CE}=\text{Rated } V_{CEO}$		1.0	mA
I_{EBO}	$V_{EB}=5.0\text{V}$		10	mA
BV_{CEO}	$I_C=200\text{mA}$ (2N6383)	40		V
BV_{CEO}	$I_C=200\text{mA}$ (2N6384)	60		V
BV_{CEO}	$I_C=200\text{mA}$ (2N6385)	80		V
BV_{CER}	$I_C=200\text{mA}, R_{BE}=100\Omega$ (2N6383)	40		V
BV_{CER}	$I_C=200\text{mA}, R_{BE}=100\Omega$ (2N6384)	60		V
BV_{CER}	$I_C=200\text{mA}, R_{BE}=100\Omega$ (2N6385)	80		V
BV_{CEV}	$I_C=200\text{mA}, V_{BE(\text{off})}=1.5\text{V}$ (2N6383)	40		V
BV_{CEV}	$I_C=200\text{mA}, V_{BE(\text{off})}=1.5\text{V}$ (2N6384)	60		V
BV_{CEV}	$I_C=200\text{mA}, V_{BE(\text{off})}=1.5\text{V}$ (2N6385)	80		V

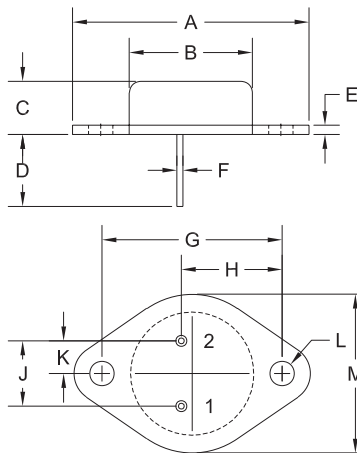
R1 (28-August 2008)

**NPN SILICON POWER
DARLINGTON TRANSISTOR**

ELECTRICAL CHARACTERISTICS - Continued: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$V_{CE(SAT)}$	$I_C=5.0A, I_B=10mA$		2.0	V
$V_{CE(SAT)}$	$I_C=10A, I_B=100mA$		3.0	V
$V_{BE(ON)}$	$V_{CE}=3.0V, I_C=5.0A$		2.8	V
$V_{BE(ON)}$	$V_{CE}=3.0V, I_C=10A$		4.5	V
h_{FE}	$V_{CE}=3.0V, I_C=5.0A$	1K	20K	
h_{FE}	$V_{CE}=3.0V, I_C=10A$	100		
V_F	$I_F=10A$		4.0	V
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		200	pF
$ h_{he} $	$V_{CE}=5.0V, I_C=1.0A, f=1.0MHz$	20		
h_{he}	$V_{CE}=5.0V, I_C=1.0A, f=1.0kHz$	1K		

TO-3 CASE - MECHANICAL OUTLINE



R2

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.516	1.573	38.50	39.96
B (DIA)	0.748	0.875	19.00	22.23
C	0.250	0.450	6.35	11.43
D	0.433	0.516	11.00	13.10
E	0.054	0.065	1.38	1.65
F	0.035	0.045	0.90	1.15
G	1.177	1.197	29.90	30.40
H	0.650	0.681	16.50	17.30
J	0.420	0.440	10.67	11.18
K	0.205	0.225	5.21	5.72
L (DIA)	0.151	0.172	3.84	4.36
M	0.984	1.050	25.00	26.67

TO-3 (REV: R2)

LEAD CODE:

- 1) Base
- 2) Emitter
- C) Collector

MARKING: FULL PART NUMBER

R1 (28-August 2008)